

**Amendments to the Specification:**

Please amend the title as follows:

METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE WITH  
CAPACITOR ELECTRODES AND METHOD OF MANUFACTURING THEREOF

Please rewrite the paragraph beginning at page 1, line 1, of the specification as follows:

This application is a divisional of Application Serial No. 09/903,735 filed July 13, 2001,  
now U.S. Patent No. 6,630,705.

Please rewrite the paragraph beginning at page 14, line 31, of the specification as follows:

As described above, in the case that copper is used as a material for the conductive material film 26a and 26b as a wiring layer the wiring resistance can be reduced since copper has the lower electric resistance value than aluminum, which is a conventional wiring material. Therefore, the occurrence of the wiring delay can be prevented. In addition, since the barrier metal layer 34a and 34b is formed materials such as copper which forms the conductive materials film 26a and 26b can be prevented from ~~defusing~~ diffusing into the sixth interlayer insulating film 23, or the like.

Please rewrite the paragraph beginning at page 18, line 11, of the specificaiton as follows:

The second interlayer insulating film 10 (see Fig. 3) is deposited on the first interlayer insulating film 7 by using a CVD method, or the like. A resist film which has a hole pattern is formed on the second interlayer insulating film 10. By partially removing the second interlayer insulating film 10 using the resist film as a mask, the contact holes 11a and 11b (see Fig. 3) are formed. The upper surface of the conductive material film 9b is exposed at the bottom of the contact hole 11a. And the conductive region 2e is exposed at the bottom of the contact hole 11b. After that, the resist film is removed. A conductive material film which fills in inside of the contact holes 11a and 11b and which extends to the upper surface of the second interlayer insulating film 10

is formed by using a ~~spattering~~ sputtering method, or the like. As for the material of the conductive material film, tungsten, for example, or the like, can be used. Part of the conductive material film which is located on the upper surface of the second interlayer insulating film 10 is removed. In this way, the conductive material film 15a and 15b is formed.